

FRED

$$V_{RRM} = 600 \text{ V}$$

$$I_{FAV} = 2 \times 30 \text{ A}$$

$$t_{rr} = 35 \text{ ns}$$

Fast Recovery Epitaxial Diode
 Low Loss and Soft Recovery
 Anti-parallel legs

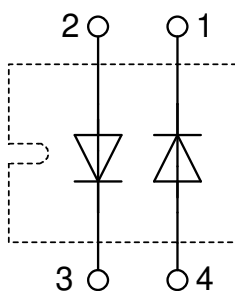
Part number

DSEI2x30-06C



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

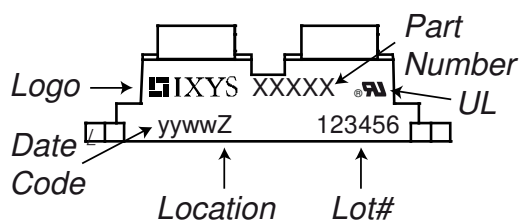
Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			100	μA	
		V _R = 480 V	T _{VJ} = 125°C			7	mA	
V _F	forward voltage drop	I _F = 30 A	T _{VJ} = 25°C			1.51	V	
		I _F = 60 A				1.68	V	
		I _F = 30 A	T _{VJ} = 150°C			1.34	V	
		I _F = 60 A				1.60	V	
I _{FAV}	average forward current	T _C = 90°C rectangular d = 0.5	T _{VJ} = 150°C			30	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.10	V	
r _F	slope resistance					7.9	mΩ	
R _{thJC}	thermal resistance junction to case					1.2	K/W	
R _{thCH}	thermal resistance case to heatsink				0.10		K/W	
P _{tot}	total power dissipation	T _C = 25°C				105	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		300	A	
C _J	junction capacitance	V _R = 600 V f = 1 MHz		T _{VJ} = 25°C	22		pF	
I _{RM}	max. reverse recovery current	} I _F = 37 A; V _R = 350 V -di _F /dt = 200 A/μs		T _{VJ} = 25 °C	5.5		A	
				T _{VJ} = 100 °C	9		A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	80		ns	
				T _{VJ} = 100 °C	150		ns	

Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				70	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		150	°C
Weight					30		g
M_D	mounting torque			1.1		1.5	Nm
M_T	terminal torque			1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2			mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V
		t = 1 minute		2500			V

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI2x30-06C	DSEI2x30-06C	Tube	10	449091

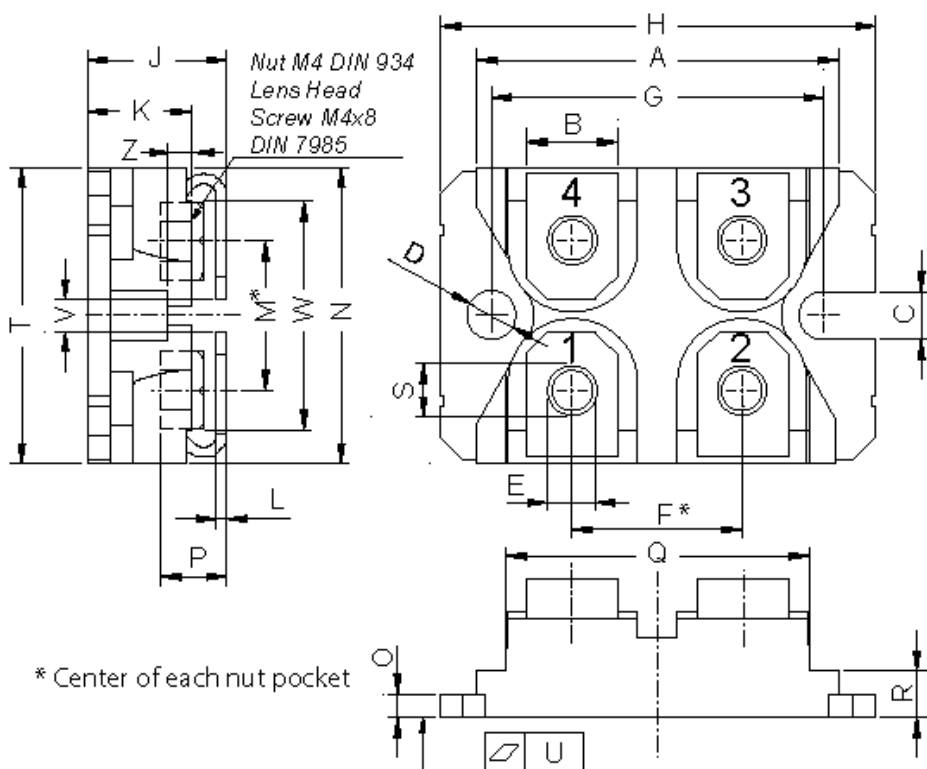
Similar Part	Package	Voltage class
DSEI2x31-06C	SOT-227B (minibloc)	600

Equivalent Circuits for Simulation

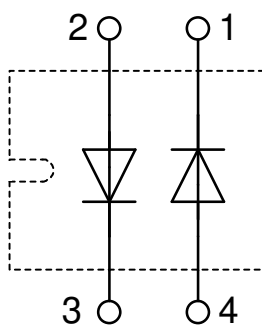
* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Fast Diode	
$V_{0\ max}$	threshold voltage	1.1	V
$R_{0\ max}$	slope resistance *	6	mΩ

Outlines SOT-227B (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



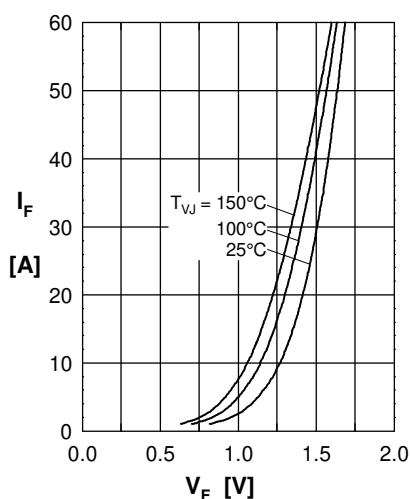
Fast Diode


Fig. 1 Forward current I_F versus max. forward voltage drop V_F

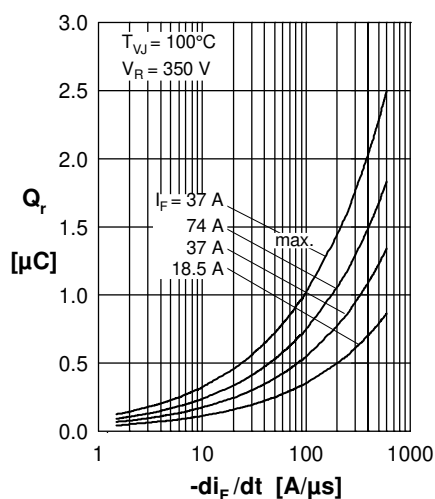


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

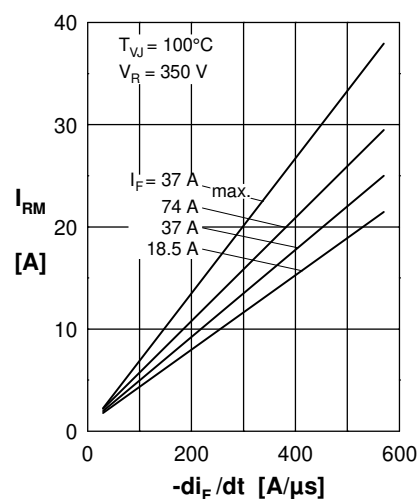


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

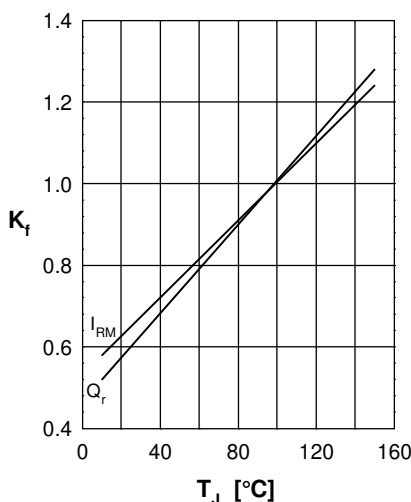


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

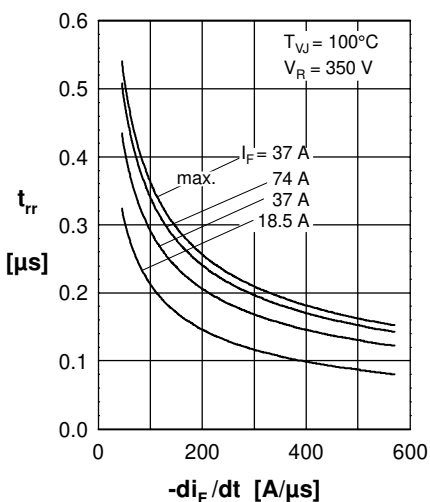


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

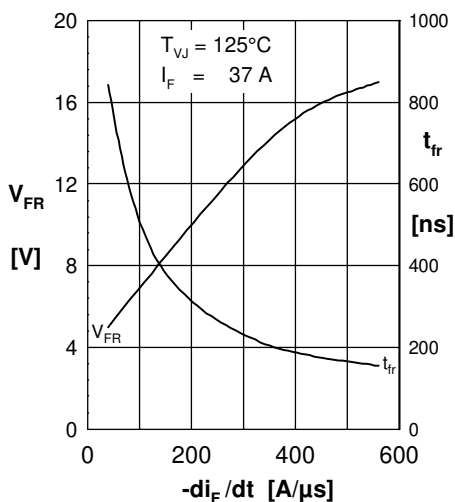


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

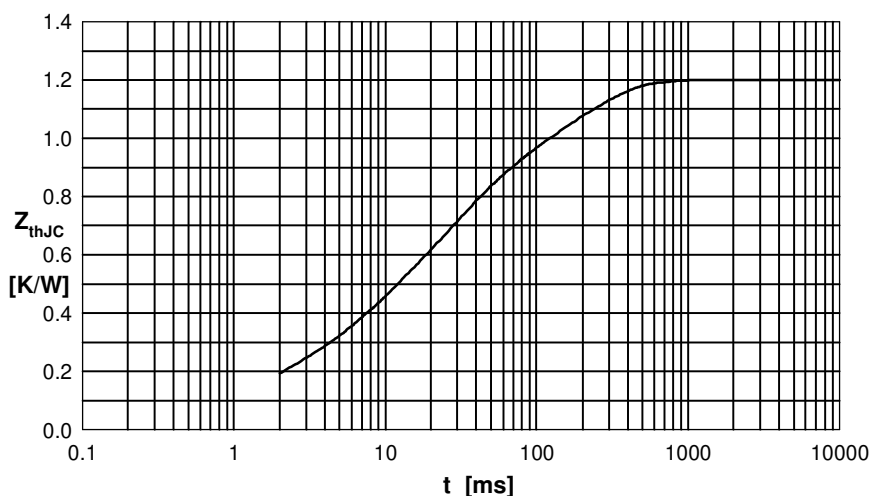


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.180	0.0050
2	0.020	0.0600
3	0.100	0.0010
4	0.400	0.1700
5	0.500	0.0230